



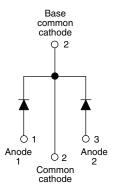
www.vishay.com

Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 2 x 8 A



TO-247AC



PRODUCT SUMMARY					
Package	TO-247AC				
I _{F(AV)}	2 x 8 A				
V _R	1200 V				
V _F at I _F	2.4 V				
t _{rr} typ.	28 ns				
T _J max.	150 °C				
Diode variation	Single die				

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC®-JESD47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS
COMPLIANT
HALOGEN
FREE
Available

BENEFITS

- · Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA16PA120C... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A per leg continuous current, the VS-HFA16PA120C... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16PA120C... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V _R		1200	V		
Maximum continuous forward current	1	T _C = 100 °C	8	А		
per device	─ I _F		16			
Single pulse forward current	I _{FSM}		130			
Maximum repetitive forward current	I _{FRM}		32			
Mayimum nauga dispination	-	T _C = 25 °C	73.5	W		
Maximum power dissipation	P_{D}	T _C = 100 °C	29	VV		
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C		



VS-HFA16PA120CPbF, VS-HFA16PA120C-N3

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ELECTRICAL SPECIFICATIONS PER LEG (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V _{BR}	Ι _R = 100 μΑ	1200	-	-		
		I _F = 8.0 A	-	2.6	3.3	V	
Maximum forward voltage	V_{FM}	I _F = 16 A	-	3.4	4.3		
		I _F = 8.0 A, T _J = 125 °C	-	2.4	3.1		
Maximum reverse		V _R = V _R rated	-	0.31	10		
leakage current	I _{RM}	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	-	135	1000	μA	
Junction capacitance	C _T	V _R = 200 V	-	11	20	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package	-	8.0	-	nH	

DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200$) A/μs, V _R = 30 V	-	28	-		
Reverse recovery time	t _{rr1}	T _J = 25 °C		-	63	95	ns	
	t _{rr2}	T _J = 125 °C	$I_F = 8.0 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	106	160		
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.5	8.0	- A - nC	
reak recovery current	I _{RRM2}	T _J = 125 °C		-	6.2	11		
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	140	380		
neverse recovery charge	Q _{rr2}	T _J = 125 °C		-	335	880		
Peak rate of recovery current during t _b	dI _{(rec)M} /dt1	T _J = 25 °C		-	133	-	A/µs	
	dI _{(rec)M} /dt2	T _J = 125 °C		-	85	-	Ανμδ	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R _{thJC}		-	-	1.7		
Thermal resistance, junction to ambient	R _{thJA}	R _{thJA} Typical socket mount		-	40	K/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased		0.25	-		
Woight			-	6.0	=	g	
Weight			-	0.21	-	OZ.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-247AC (JEDEC)	HFA16PA120C				

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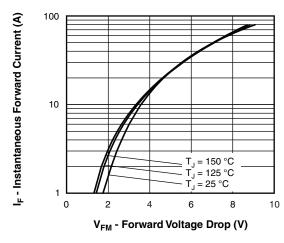


Fig. 1 - Maximum Forward Voltage Drop Characteristics

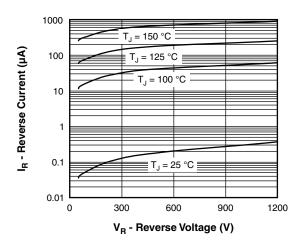


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

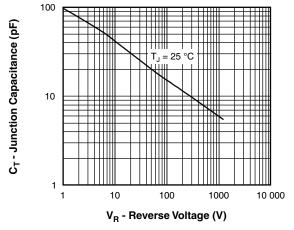


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

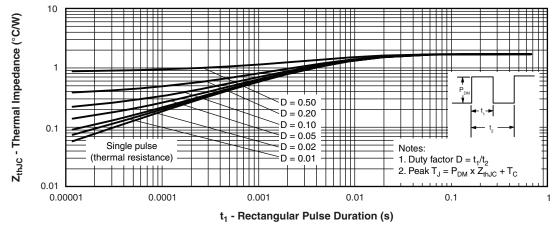
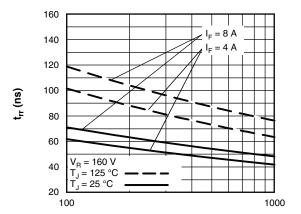


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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dl_F/dt (A/μs)
Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

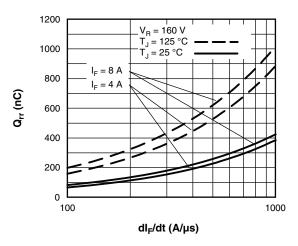


Fig. 7 - Typical Stored Charge vs. dl_F/dt

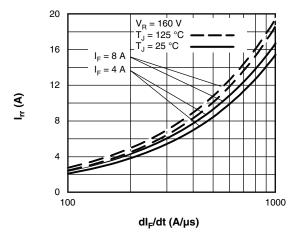


Fig. 6 - Typical Recovery Current vs. dl_F/dt

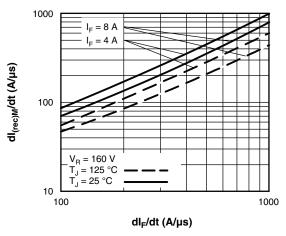


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

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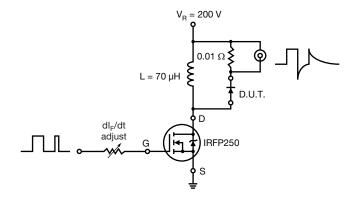
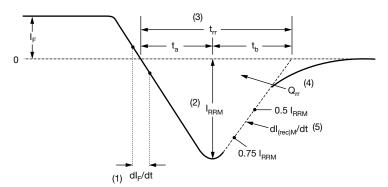


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RBM} and 0.50 I_{RBM} extrapolated to zero current.
- (4) ${\rm Q_{rr}}$ area under curve defined by ${\rm t_{rr}}$ and ${\rm I_{RRM}}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

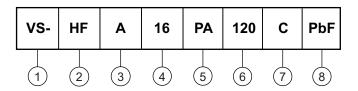
Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code



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2 - HEXFRED® family

Electron irradiated

Current rating (16 = 16 A)

5 - PA = TO-247AC

6 - Voltage rating: (120 = 1200 V)

7 - Circuit configuration

C = Common cathode

7 - Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-HFA16PA120CPbF	25	500	Antistatic plastic tube				
VS-HFA16PA120C-N3	25	500	Antistatic plastic tube				

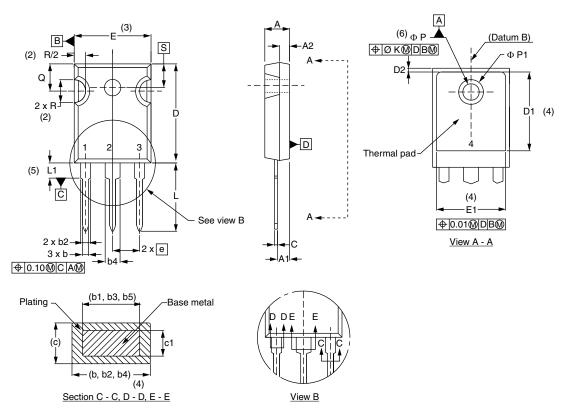
LINKS TO RELATED DOCUMENTS					
Dimensions		www.vishay.com/doc?95542			
Part marking information	TO-247ACPbF	www.vishay.com/doc?95226			
Part marking information	TO-247AC-N3	www.vishay.com/doc?95007			



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TO-247AC - 50 mils L/F

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	MILLIMETERS		INCHES	
STWIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.17	1.37	0.046	0.054	
р	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIN	MILLIMETERS		INCHES	
OTIVIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.35	0.020	0.053	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46	BSC	0.215	BSC	
ØK	0.254		0.010		
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	-	7.39	-	0.291	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC 0.217 BSC				

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- $^{(7)}$ Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q



Legal Disclaimer Notice

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